

10G-PON ONU/OLT Chipset

M02180

- All-in-one 10G/10G low power burst mode laser driver + limiting amplifier with integrated CDR
- Integrated EEPROM, DDMI controller and APD DC-DC controller
- Low power operation <100 mA
- 10G Dual-Closed-Loop (DCL) laser driver operation
- Integrated laser safety features and laser shutdown switch

M02172

- Low power 11.3G EML driver with single 3.3 V supply
- EML driver with up to 2.2 Vpp single-ended output swing
- Programmable laser bias current up to 150 mA
- In low cost 5 x 5 mm QFN package
- Can be used to differential drive an L-PIC EOML

M02142

- 11.3G Low power burst mode limiting Amplifier
- 3 mV input sensitivity at 11.3 Gbps
- Fast data settling and fast LOS output
- In low cost 3 x 3 mm QFN package

MATA-02135

- 10G Low power and high sensitivity TIA
- Typical 30 mA at +3.3 V
- Typical -33 dBm sensitivity with APD at 1e-3 BER
- Support PINA or PINK based RSSI

MAMF-011095

- L-PIC controller chip
- I2C interface
- Array of ADC and DACs

MATA-02238

- New gen low power 10.3G dual date burst mode TIA
- Typical -32 dBm sensitivity with APD at 1e-3 BER
- Selection between fixed rate (10G mode only) or dual rate (1G/10G mode)

157D-10C-LT6CD

- Electro-Optic Modulated Laser (EOML)
- SiPh-based L-PIC chip integrates 1577 nm CW DFB laser, MZ modulator, monitor photodiode, and temperature sensor
- Available in a hermetic TO-60 package with thermoelectric cooler (TEC)
- Auto calibration and programmable performance via controller chip

APD10B and APD10B/ES

- Avalanche photodiode chip or CoC
- High data rate, up to 11.3 Gbps
- High sensitivity to -29.5 dBm for ES version
- Vbr Temperature coefficient = 14 mV/C°
- 1250 to 1650 nm wavelength range
- 10G EPON, XG PON, XGS PON OLT and ONU applications

127D-10I-LT5CC

- Directly modulated 10Gbps Distributed Feedback (DFB) laser diode devices at 1270 nm
- Available in hermetic TO-56 package with aspherical lens (10.1 mm focal length), and co-packaged InGaAs monitoring photodiode

127D-02I-VT5AB

- Directly modulated 2.5 Gbps 1270 nm DFB Narrow Farfield (NFF) laser diode chips
- Available with aspherical lens cap (FL=7.5 mm) in hermetic TO-56 package, integrated InGaAs monitoring photodiode and Type B pinout (common anode)

